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Advanced Ceramics Progress

Journal Homepage: www.acerp.ir

Original Research Article

Effect of Sintering Parameters on the Densification of ZrB₂-SiC based CompositeElnaz Irom ^a, Mohammad Zakeri ^{b*}, Mansour Razavi ^c^a PhD Candidate, Department of Ceramics, Materials and Energy Research Center, Karaj, Iran.^b Associate Professor, Department of Ceramics, Materials and Energy Research Center, Karaj, Iran.^c Professor, Department of Ceramics, Materials and Energy Research Center, Karaj, Iran.* Corresponding Author Email: m_zakeri@merc.ac.ir (M. Zakeri)URL: https://www.acerp.ir/article_211776.html

ARTICLE INFO

ABSTRACT

Article History:

Received: 27 July 2024

Revised: 28 August 2024

Accepted: 01 September 2024

Keywords:

ZrB₂,
Densification,
Spark Plasma Sintering,
Porosity,
Density

In this study, ZrB₂-SiC ultra-high temperature ceramic composite was sintered using Spark Plasma Sintering (SPS) process with WC/HfB₂ modifiers at different sintering temperatures of 1850, 1900, 2000, and 2050°C for 8 and 25 minutes. The densification behavior of the composite was also examined using punch displacement-time and temperature-time measurement graphs during SPS. Phase and microstructure evaluations were also done based on XRD, EDS, and FESEM methods. The effect of SPS parameters on the densification of ZrB₂-SiC-based composite was studied. In this case, there was no displacement until the pressure was applied due to the low sinterability of boride powders. A ZrB₂-SiC-based composite with a relative density of 90% was obtained at 2050°C under 30 MPa for a 25-minute soaking time. The densification curve of this sample showed a typical “S” shape. The best water absorption and apparent porosity values obtained as 1.3 and 6.7%, respectively. The minimum and maximum punch displacement of the samples was 2.2 and 3.6 mm, respectively. Use of WC/HfB₂ modifiers led to the formation of byproducts of WB and HfB.

<https://doi.org/10.30501/acp.2024.465234.1158>

1. INTRODUCTION

High-temperature applications require structural ceramic composite parts that can withstand harsh environmental situations. Highly refractory materials, such as Ultra-High Temperature Ceramics (UHTCs) family, are some of the most encouraging candidates. They possess an acceptable functional, physical, and mechanical properties including considerable flexural strength, hardness, and fracture toughness, and very high melting point (>3000°C). The new generation of thermal protection systems is designed to resist high heat flux, high temperature, and mechanical stress. Additionally, they should exhibit good heat shock

resistance, oxidation resistance, and ablation resistance ([Chakraborty et al., 2016](#); [Jin et al., 2018](#)).

Various consolidation processes have been employed to sinter the UHTCs, including pressure-less sintering ([Wang et al., 2022](#)), flash sintering ([Foroughi et al., 2022](#)), reactive hot pressing ([Lu et al., 2016](#)), hot pressing ([Zou et al., 2013](#)), Spark Plasma Sintering (SPS) ([Thimmappa et al., 2019](#)), and reactive SPS ([Zhu et al., 2022](#)). High-density UHTCs without sintering aids can be obtained by SPS with limited grain growth ([Bellosi et al., 2006](#); [Guo et al., 2008](#)).

ZrB₂ is a key material with a lower density than other metal diboride ceramics. Pure ZrB₂ and modified ZrB₂ are considered potential alternatives for the last

Please cite this article as: Irom, E., Zakeri, M., & Razavi, M. (2024). Effect of Sintering Parameters on the Densification of ZrB₂-SiC based Composite, *Advanced Ceramics Progress*, 10(3), 8-14. <https://doi.org/10.30501/acp.2024.465234.1158>

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generations of heat-resistant structural materials. However, the ablation resistance of ZrB₂ is a challenging aspect of its performance in the field. SiC is regularly added to ZrB₂ to enhance its oxidation resistance ([Carney et al., 2009](#); [Fahrenholtz & Hilmas, 2012](#); [Han et al., 2007, 2008](#)).

Although many variations in UHTC compositions have been formulated to improve their high-temperature properties, few studies have focused on enhancing their densification along with other properties without additives. Based on previous works and our recent study, we produced a new ZrB₂-SiC composite, which is anticipated to exhibit better thermal properties and densification without adding sintering aids. The overall objective of this project was to examine the densification behavior of the HfB₂/WC modified ZrB₂-SiC bulk composite, produced through the SPS method. It is expected that using a higher sintering temperature and soaking time can improve the densification of this composite.

2. MATERIALS AND METHODS

Boride powders of ZrB₂ (99.9%, 3 μm), HfB₂ (99.9%, 5 μm), and carbide powders of SiC (99%, 70 nm), and WC (99%, 5 μm) were mixed in specific ratios (64.75 vol.% ZrB₂, 27.75 vol.% SiC, 5 vol.% WC, and 2.5 vol.% HfB₂) based on our previous works ([Irom, 2023](#); [Shalmani et al., 2021](#)). Dispersion evolution was carried out in an ultrasonic bath for 30 min. After the mixing stage, the obtained suspension was homogenized in a heater-magnetic stirrer (Heidolph MR 3001, Germany) for 120 minutes. The composite powder mixture was then completely dried in an oven at 120 °C for 6 h. Consequently, the dried powder was sieved and poured into a graphite die with a diameter of 3 cm. The inner surface of the die was entirely covered with graphite foil. The sintering stage was performed by the SPS apparatus (SPS-20 T-10, Easy Fashion Metal Products Trade Co., China) in a vacuum atmosphere, with the chamber pressure monitored. The temperature of the graphite die was recorded with an optical pyrometer (Raytek, USA). Between room temperature and 1600 °C, with a heating rate of 50 °C/min, a primary uniaxial pressure of 10 MPa was used on the die. At the maximum SPS temperature (1850°C-2050°C), the applied pressure was gradually increased up to 30 MPa and maintained for 8 or 25 min. To treat the surface of the as-sintered sample, consequent grinding and polishing were operated on both sides. X-Ray

Diffraction (PW3710, Philips, Netherlands) was utilized for crystalline phase characterization.

The microstructure of the samples was evaluated by Field Emission Scanning Electron Microscopy (FESEM) (TESCAN Mira 3-XMU, Czech Republic). Energy-Dispersive X-Ray Spectroscopy (EDS) analysis was then carried out for the semi-quantitative assessment of the composition of phases.

3. RESULTS AND DISCUSSION

Table 1 presents the relative density, water absorption, and porosity of sintered samples. As observed, the relative density increased with an increase in the sintering temperature. Consequently, both water absorption and porosity decreased with the progress in the relative density. Boride ceramics have low self-diffusion and are difficult to sinter ([Venkateswaran et al., 2006](#)). The SPS method significantly reduced the porosity and increased the relative density of this type of material due to the simultaneous application of mechanical pressure and heat during sintering. It should be noted that spark plasma discharges during SPS sintering clean the surfaces of the powders from CO₂ and H₂O that have already been absorbed, as well as the impurities that remain on the surface of the particles during powder synthesis, such as B₂O₃ or ZrO₂, and HfO₂. In the subsequent stages, the presence of clean and active surfaces increases the penetration of grain boundaries, which, together with spark plasma discharges, improves the transfer of matter and facilitates the condensation and growth of grains ([R. Riedel and I.W. Chen, 2011](#)). Higher temperature and soaking times provide more activation energy, removing the oxide impurities of the surface of the powder particles, resulting in the interaction of the composite powders. In this regard, active and clean surfaces accelerated grain boundary diffusion.

An experimental SPS parameter monitoring for ZSWH1 and ZSWH4 is represented in Figure 1, where not only the displacement was recorded but also the temperature, DC current, applied pressure, and vacuum pressure was monitored. As seen, the chamber pressure changed during the sintering process due to gas removal from the die system. The gas release at low temperature is caused by adsorbed water vapor and trapped air in the mixed powder while at high temperature, it originates from chemical reaction and gaseous byproducts. There is a peak at the beginning of the process which can be attributed to inappropriate mold preparation and powder pull-out in the chamber.

TABLE 1. Relative density water absorption porosity of samples

Sample	sintering Temperature (°C)	Soaking time (min)	Relative Density (%)	Water absorption (%)	Apparent Porosity (%)
ZSWH1	1850	8	67.8	6.9	27.6
ZSWH2	1900	8	73.0	5.8	24.9
ZSWH3	2000	25	83.5	3.2	15.8
ZSWH4	2050	25	90.8	1.3	6.7

Once the displacement increased and densification started, the chamber pressure decreased. In both graphs, the vacuum fluctuated, and the chamber pressure in the beginning of the process around 1100°C increased due to the formation of SiO and CO gases. The electrical current was gradually increased at the determined temperature and controlled until the sintering finished. Then, the DC current decreased with the rate of 0.2 KA/min.

The study of the displacement-time and temperature-time graph for sintering provides useful information. An increase in displacement indicates an increase in the powder shrinkage and provides a scale of condensation and sintering. The displacement values for ZSWH1 (Fig.1.a) and ZSWH4 (Fig.1b) were 2.2 mm and 3.6 mm, respectively. The densification curve of ZSWH4 shows a typical “S” shape.

To better study the graphs, they were divided into three zones based on displacement variations: Zone 1: there was no displacement, and the electrical power created joule heat, which warmed the die and the powder. Interestingly, no displacement occurred until the pressure was imposed mainly due to not using the sintering aids in the composition and covalent bonding, weak self-diffusion and consequently, low sinterability of the boride and carbide powders (Venkateswaran et al., 2006). There is an expansion zone in the displacement graphs as the process started, and the die temperature rose. As the temperature increased, the powder became smooth due to electrical pulses and heat. Zone 2: for ZSWH4, about 14 min after starting the process and when the temperature reached 1900°C, the displacement improvement was observed upon increasing the pressure. As a result of plastic deformation and powder shrinkage, displacement was intensified, and the maximum displacement was obtained upon applying the pressure. Zone 3: in the ZSWH4 graph, where the temperature is 2050°C and constant, the sintering process continued by diffusion and grain growth mechanism (Chaim, 2007; Marder et al., 2011). The low shrinkage in this zone can be attributed to the diffusion mechanism mainly because the diffusion is a slow and time-consuming process (Chaim, 2007; Marder et al., 2011). The SPS sensors cannot record the minor displacement variations; therefore, no displacement was observed in the third zone. Over time in this stage and grain growth, the porosity decreased while the relative density increased. Once the soaking time ended, the temperature was slowly reduced, and the pressure was gradually removed at 1600°C. A comparison between the displacement and temperature graphs of the two samples reveals that after the end of the soaking time at the maximum temperature in the ZSWH1, the displacement did not remain constant. As a result, the densification process continued while the soaking time was not enough at this temperature. However, in the ZSWH4, prior to the end

of the soaking time, the graph became stable, and the condensation continued with reduction in both the grain growth and porosity. It seems that the soaking time should be chosen in such a way that displacement becomes constant before the end of the time, and the displacement graph remains a little more fixed at the highest temperature. At this stage, the changes are insignificant, and the device cannot record them. The overlap of displacement and temperature graphs in the soaking region indicates the last step of sintering, i.e., grain growth and diffusion. In this area, i.e., at the maximum temperature and where the displacement is constant, the sample should be maintained for a few minutes until the sintering is complete.

Stabilization of displacement during cooling and non-overlapping of displacement graph with the temperature diagram in the soaking area is not desirable. Soaking time should be determined in such a way that displacement becomes constant within the soaking stage and grain growth occurs.

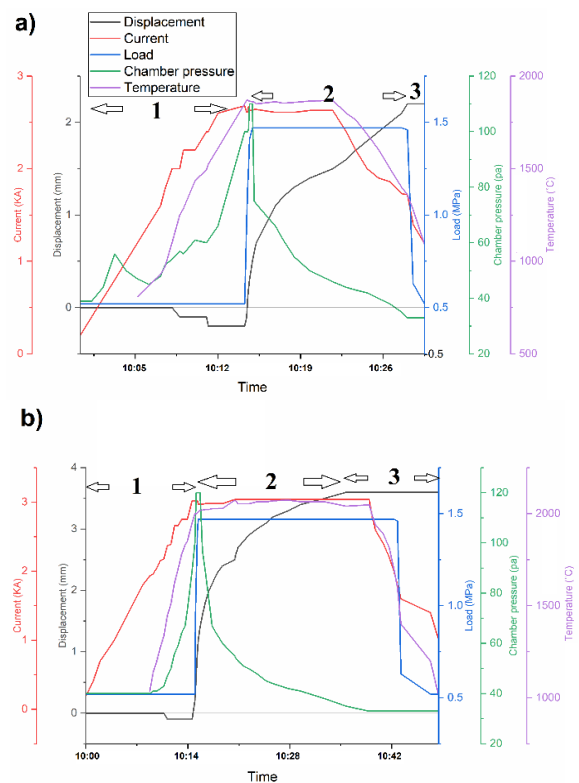
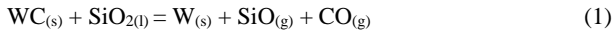


Figure 1. The displacement-time and temperature-time graph for sintering of a) ZSWH1 b) ZSWH4

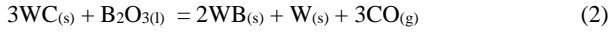
Figure. 2 shows the XRD patterns of the as-sintered ZSWH3 sample. The composite consists of ZrB₂, SiC, and byproducts of WB and HfB. During the sintering process, WC and HfB₂ were converted into WB and HfB, respectively, as discussed below:

Under thermodynamical investigations, Monteverde et al. reported that WC interacted with superficial oxides of the ZrB₂ particles like molten SiO₂, as shown

in Reaction (1) at temperatures as low as 1130 °C and chamber pressure of about 100 Pa (Monteverde & Silvestroni, 2016).

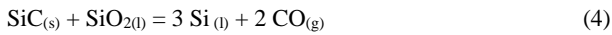
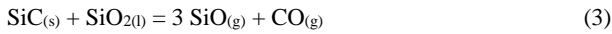


where WC and B₂O₃ oxide impurities originating from ZrB₂ and HfB₂ powders can react with each other based on Reaction (Irom, 2023):



On the other hand, Ding et al. indicated that at temperatures higher than 1700 °C, diffusion of B into W increased, hence formation of the WB phase (Ding et al., 2020). Free W element can also interact with HfB₂. It seems that penetration of B element from HfB₂ into W resulted in the creation of boron vacancies in HfB_{2-x}, coupled with the formation of HfB phase. Residual boron vacancies can lead to a qualified sintering process. More details about these interactions can be found in our previous work (Irom, 2023).

Beside WC/HfB₂ modifiers, SiC can act significantly followed by introduction of self-cleaning reactions between SiC and its surface oxide, i.e., SiO₂. In the same way, Reaction 3 occurs under standard conditions i.e., at the pressure of p=10⁵ Pa and temperatures between 1527- 1677°C. Reactions 3 and 4 occur at temperatures above 1677°C, and surface SiO₂ impurity can be either eliminated (Shafagh et al., 2021).



Based on Reaction 5, SiC can react with contaminations at temperatures above 1800°C (Shafagh et al., 2021):

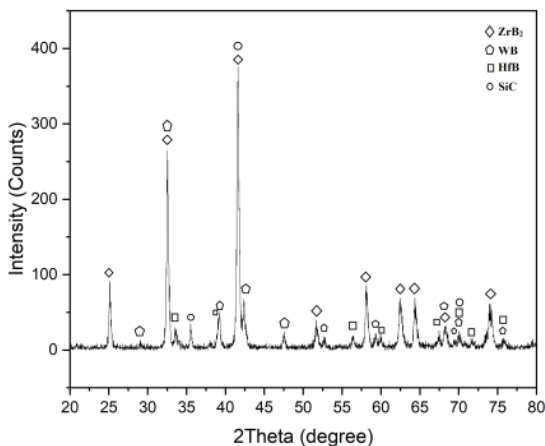
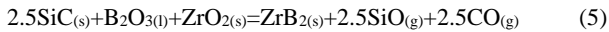


Figure 2. XRD patterns of the sample ZSWH3

Figure 3.a illustrates the secondary FESEM images of the polished surface of the ZSWH3. The sample shows a mosaic microstructure with a proper distribution of reinforcing phases within the ZrB₂ matrix. In Figure 3, the porosities are shown by arrows

on the surface. Porosities are uniformly distributed through the surface.

Figure 3.b shows the backscattered FESEM image in a higher magnification.

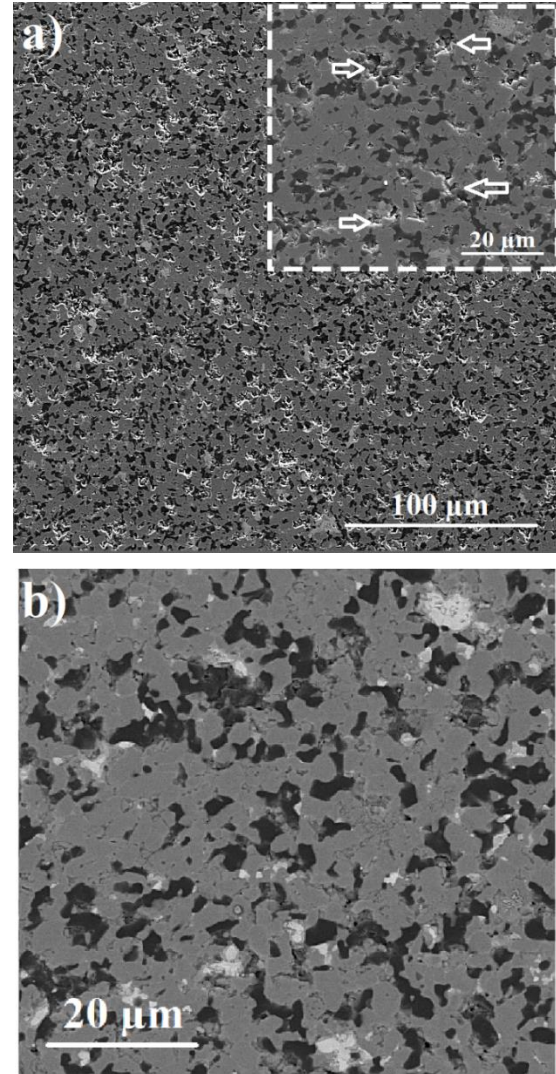


Figure 3. a) secondary, b) backscattered FESEM micrograph of the polished surface of the ZSWH3

Figure 4 represents the map analysis which was carried out to specify the phases. As indicated, the black phases are rich in Si which can be attributed to SiC. Light grey phase is rich in Hf and dark grey in Zr. To precisely determine the phases, point EDS analysis was done and according to different colors, five points were recognizable. As represented in Figure 5. (b), four various phases can be identified in the sample. Point A is attributed to SiC, point B to HfB, points C and D to ZrB₂, and point E to WB. The gray matrix is ZrB₂, and SiC, WB, and there is a slight weight percentage of W in the EDS of points of C and D.

Figure 5 confirms the presence of WB and HfB phases based on the XRD and EDS analyses. A

comparison of the points B and D reveals that the weight percentages of Zr and Hf in point C were 44.80 and 1.82% and in point D, they were 30.03 and 16.95%, respectively. It seems that Hf was diffused into the ZrB₂ grains during sintering, as already reported by Balak et

al. (Balak, 2019). The W content of point D is also higher than that of point C which can be associated with the diffusion of W into the ZrB₂ grains. The free W element originating from Reactions 1 and 2 are also diffused into the matrix structure.

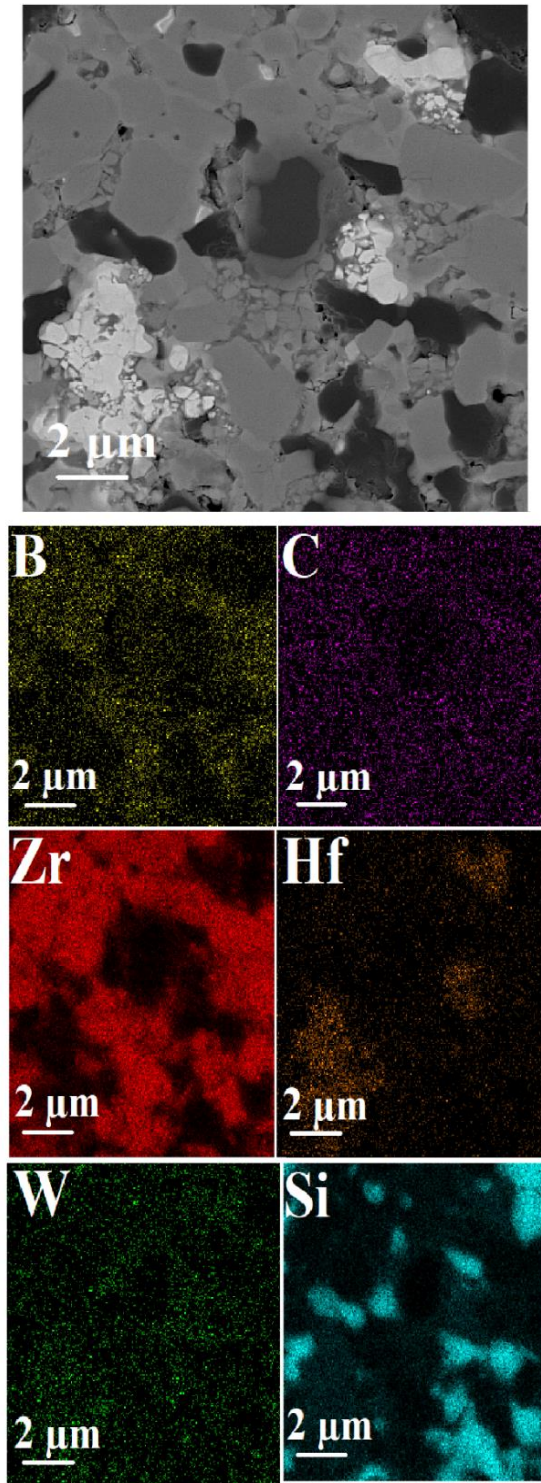


Figure 4. Map analysis of the ZSWH3

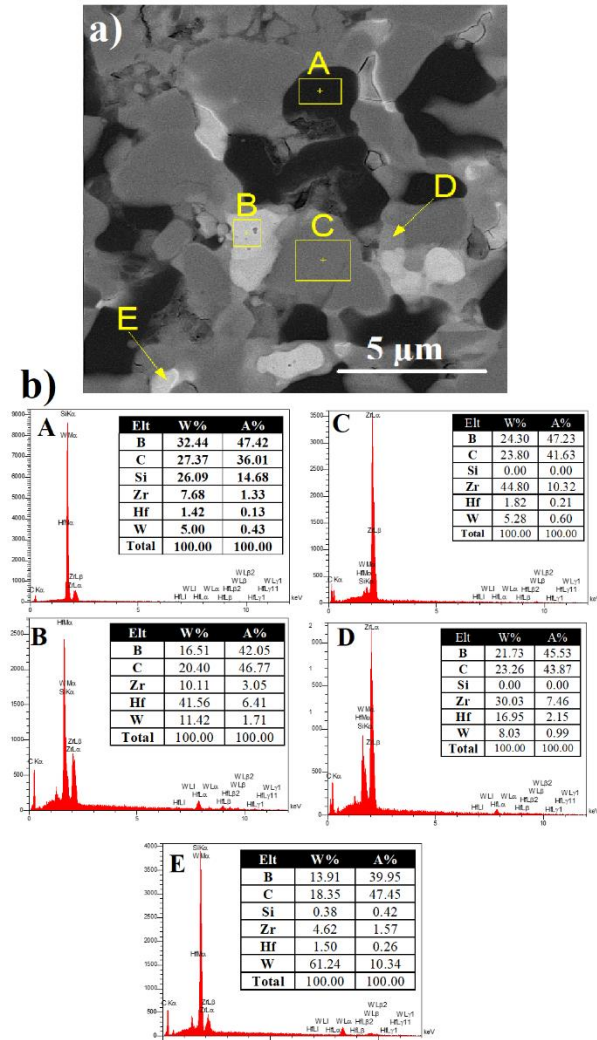


Figure 5. a) backscattered FESEM micrograph of the polished surface of the ZSWH3 B) EDS point analysis of the ZSWH3

4. CONCLUSION(S)

In this research, the ZrB₂-SiC composite was spark-plasma-sintered using WC/HfB₂ modifiers and Spark Plasma Sintering (SPS) method. The major findings are summarized in the following:

- New phases of WB and HfB were created during SPS. Followed by the diffusion of B into W, the WB phase was formed. It seems that penetration of B element from HfB₂ into W resulted in the creation of boron vacancies in HfB_{2-x}, coupled with the formation of HfB phase. WC and HfB₂ Modified the microstructure of ZrB₂-SiC by removing oxide contamination.

- Sintering the ZrB₂-SiC composite with boride or carbide modifiers needs a high temperature and soaking time. Increasing the sintering time and temperature led to higher final relative density.
- The densification behavior was examined based on the proposed densification mechanisms, and the densification was enhanced in three steps: plastic deformation, diffusion, and grain growth.
- When using four boride compounds, the last stage of sintering takes more time. In other words, diffusion and grain growth take more time to start and evolve.
- Interestingly, there was no displacement until the pressure was applied. It can be due to the low sinterability of boride powders and not using the sintering aids.
- The overlapping of the displacement and temperature diagram, which was actually indicative of the final stage of sintering, i.e., grain growth and diffusion, was necessary for sintering and completing condensation.

ACKNOWLEDGEMENT

This article has been extracted from the research project in the name of “Investigation of ablation and oxidation resistance of ZrB₂-SiC composite doped with WC and HfB₂” which was supported by Materials and Energy Research Center.

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